



Product data sheet

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SOT-23-3L

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Features

- -20 V,-4.5A, RDS(ON)=40mΩ@VGS=-4.5V
- *Improved dv/dt capability*
- Fast switching
- Green Device Available

Applications

- Notebook
- Load Switch
- Hend-Held Instruments

BVDSS	RDSON	ID
-20V	40mΩ	-4.5A

Absolute Maximum Ratings Tc=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-20	V
Vgs	Gate-Source Voltage	±12	V
	Drain Current – Continuous (Tc=250)	-4.5	A
ID	Drain Current – Continuous (Tc=1000)	-2.7	A
Ідм	Drain Current – Pulsed ¹	-18	A
D	Power Dissipation (T _c =250)	1.5	W
Po	Power Dissipation – Derate above 250	0.012	W/ C
T _{STG}	Storage Temperature Range	-55 to 150	°C
ТJ	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
Reja	Thermal Resistance Junction to ambient		80	C/ W





Off Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-20			V
	BV _{DSS} Temperature Coefficient	Reference to 250 $, I_D$ =-1mA		-0.02		V/ C
	Drain-Source Leakage Current	V _{DS} =-20V , V _{GS} =0V , T _J =250			-1	uA
IDSS Drain-Source Leakage Current		V _{DS} =-16V , V _{GS} =0V , T _J =1250			-10	uA
I _{GSS}	Gate-Source Leakage Current	V_{GS} = ±12V , V_{DS} =0V			±100	nA

On Chara	On Characteristics					
R _{DS(ON)}	RDS(ON) Static Drain-Source On-Resistance	V _{GS} =-4.5V , I _D =-3A		40	52	mΩ
TOS(ON)		V _{GS} =-2.5V , I _D =-2A		47	65	
V _{GS(th)}	Gate Threshold Voltage	──	-0.3	-0.65	-1.0	V
${}^{\vartriangle}V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	VGS-VDS , ID2500A		2		mV/ C
gfs	Forward Transconductance	V _{DS} =-10V , I _S =-3A		7		S

Dynamic	Dynamic and switching Characteristics					
Qg	Total Gate Charge ^{2,3}			9.6		
Qgs	Gate-Source Charge ^{2,3}	$V_{\text{DS}}\text{=-10V}$, $V_{\text{GS}}\text{=-4.5V}$, $I_{\text{D}}\text{=-3A}$		1.6		nC
Q _{gd}	Gate-Drain Charge ^{2,3}			2		
T _{d(on)}	Turn-On Delay Time ^{2 , 3}			6		
Tr	Rise Time ^{2,3}	V _{DD} =-10V , V _{GS} =-4.5V , R _G =25Ω		21.6		nS
T _{d(off)}	Turn-Off Delay Time ^{2 , 3}	ID=-1A		51		110
Tf	Fall Time ^{2, 3}			13.8		
Ciss	Input Capacitance			850		
Coss	Output Capacitance	V_{DS} =-10V , V_{GS} =0V , F=1MHz		70		pF
Crss	Reverse Transfer Capacitance			55		

Drain Source Diode Characteristics and Maximum Ratings

Symbol	Parameter Conditions		Min.	Тур.	Max.	Unit
ls	Continuous Source Current	V _G =V _D =0V . Force Current			-4.5	А
lsм	Pulsed Source Current	vg-vb-uv, Force Current			-9.0	А
V _{SD}	Diode Forward Voltage	V_{GS} =0V , I _S =-1A , T _J =250			-1.2	V

Note :

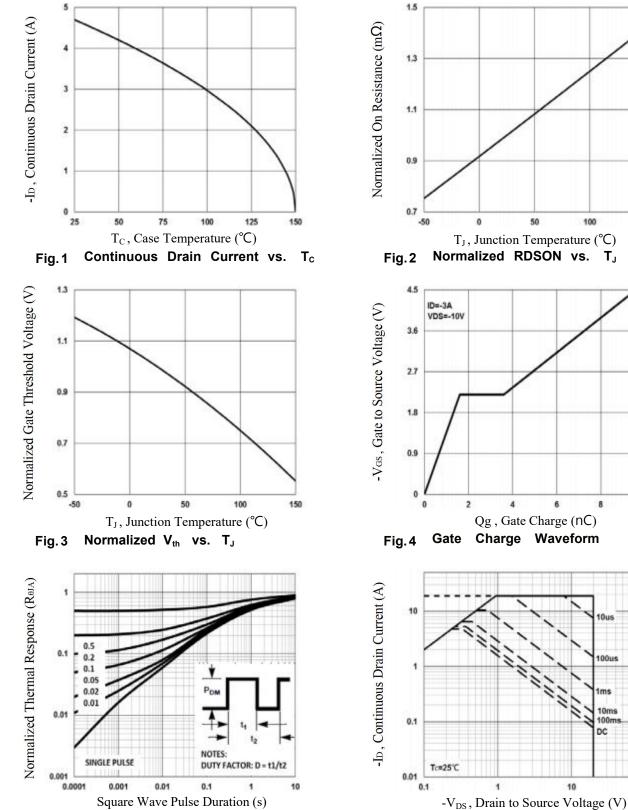
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.

2. The data tested by pulsed , pulse width $\leq~300\,\text{us}$, duty cycle $\leq~2\%.$

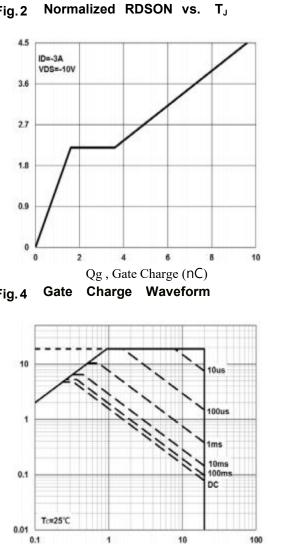
3. Essentially independent of operating temperature.











Maximum Safe Operation Area

Fig.6

50

100

150





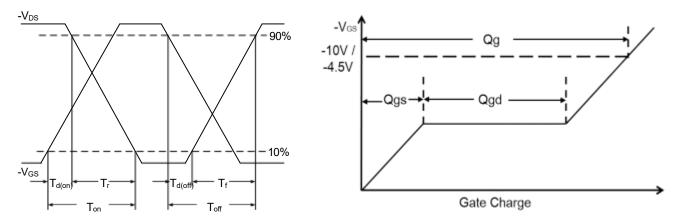


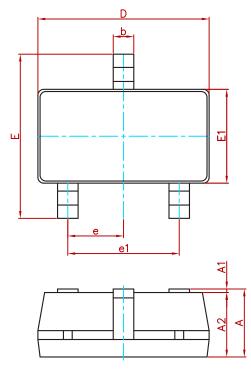
Fig. 7 Switching Time Waveform

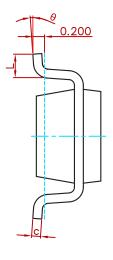
Fig. 8 Gate Charge Waveform





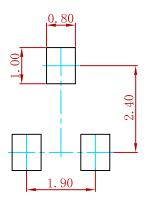
PACKAGE MECHANICAL DATA





Symbol	Symbol Dimensions In N		Dimension	s In Inches
Symbol	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
е	0.950(BSC)	0.037((BSC)
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
AO3415	SOT-23-3L	3000





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